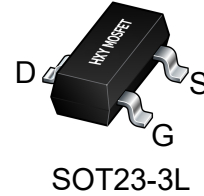




Description

The HXY5N10MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = 100V$ $I_D = 5A$

$R_{DS(ON)} < 98 m\Omega @ V_{GS}=10V$

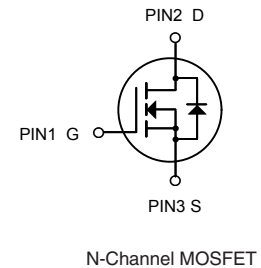
$R_{DS(ON)} < 120m\Omega @ V_{GS}=4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY5N10MI	SOT23-3L	1005	3000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	5	A
I _{DM}	Drain Current-Pulsed (Note 1)	20	A
P _D	Maximum Power Dissipation	1.5	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 To 175	°C
R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 2)	100	°C/W



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =3A	-	89	98	mΩ
		V _{GS} =4.5V, I _D =3A	-	102	110	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C _{oss}		-	24	-	PF
Reverse Transfer Capacitance	C _{rss}		-	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, R _L =19Ω V _{GS} =10V, R _G =3Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	4	-	nS
Turn-Off Delay Time	t _{d(off)}		-	20	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =3A, V _{GS} =10V	-	20	-	nC
Gate-Source Charge	Q _{gs}		-	2.1	-	nC
Gate-Drain Charge	Q _{gd}		-	3.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	3	A

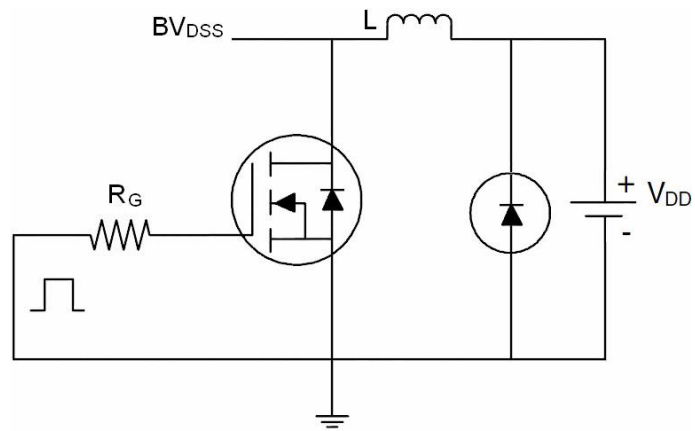
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

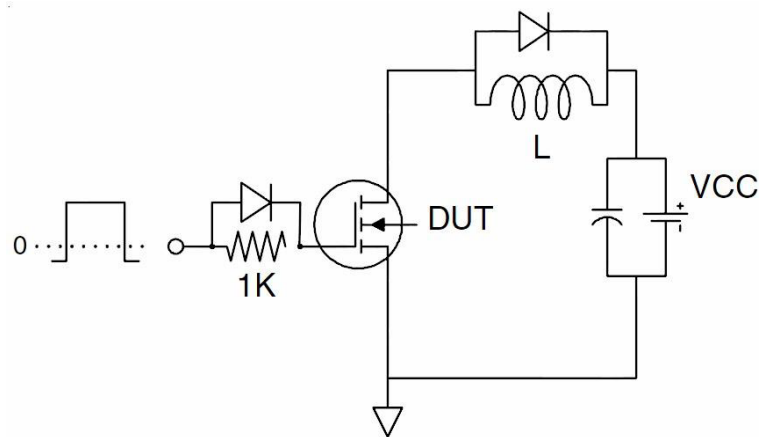


Test Circuit

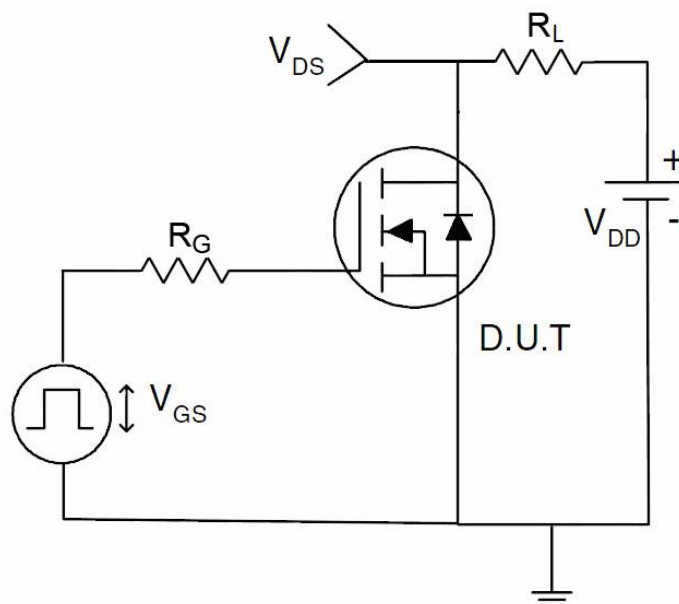
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

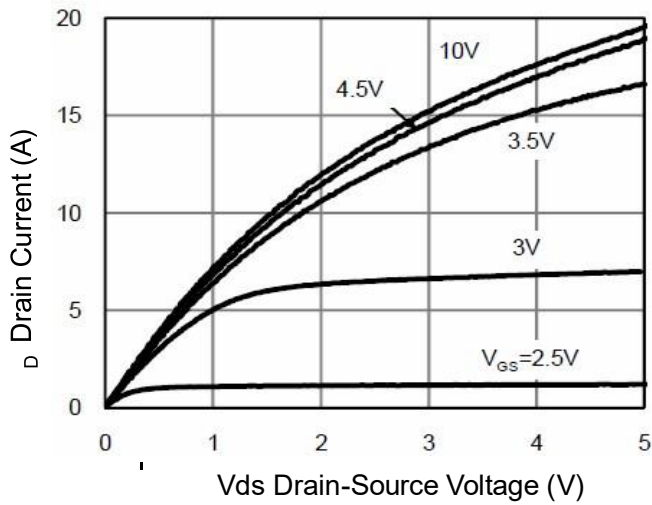


Figure 1 Output Characteristics

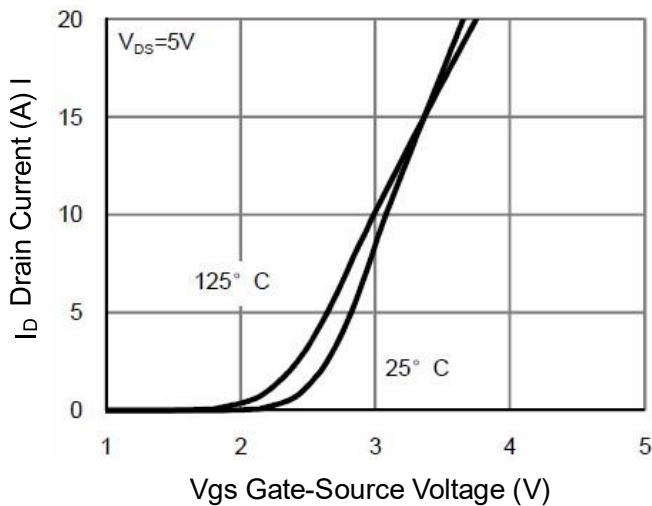


Figure 2 Transfer Characteristics

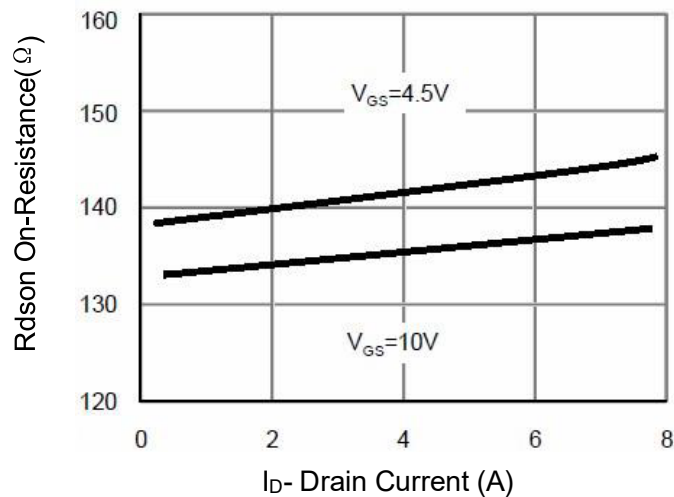


Figure 3 Rdson- Drain Current

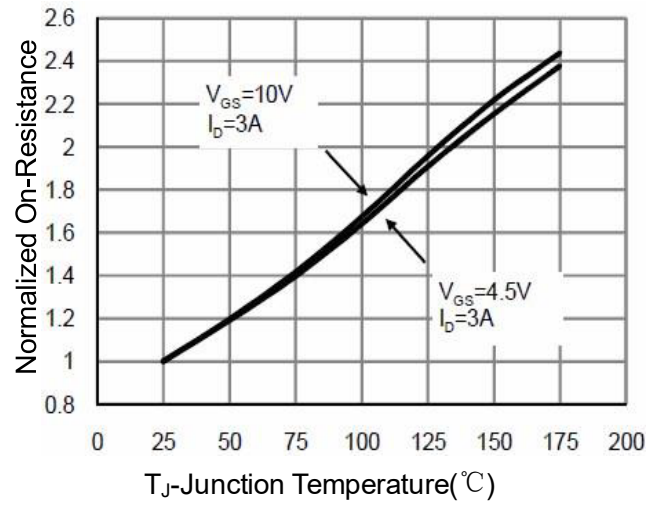


Figure 4 Rdson-Junction Temperature

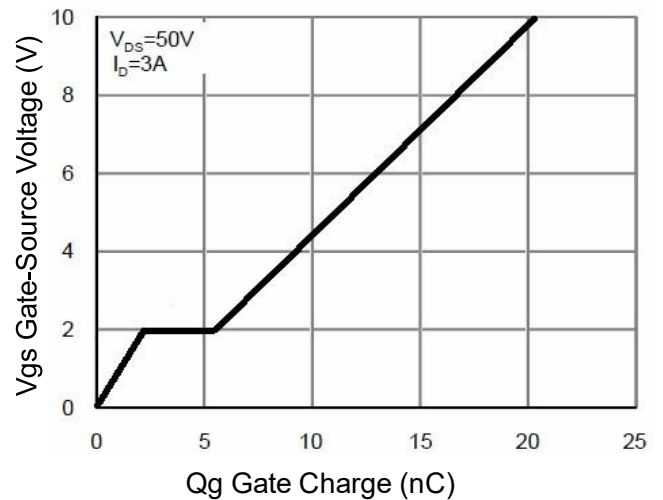


Figure 5 Gate Charge

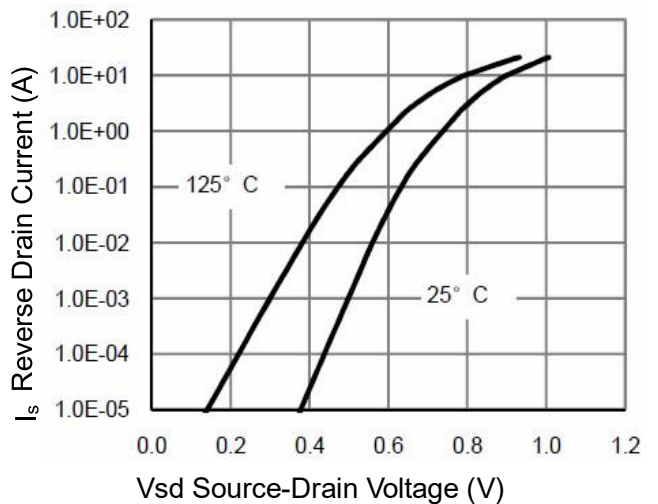


Figure 6 Source- Drain Diode Forward

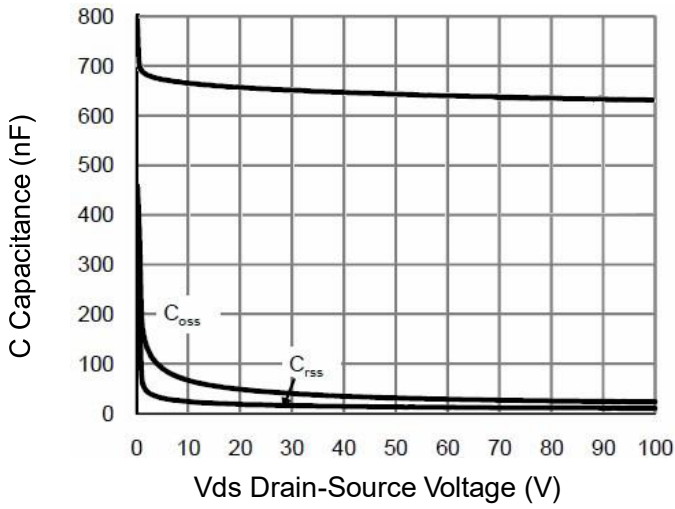


Figure 7 Capacitance vs Vds

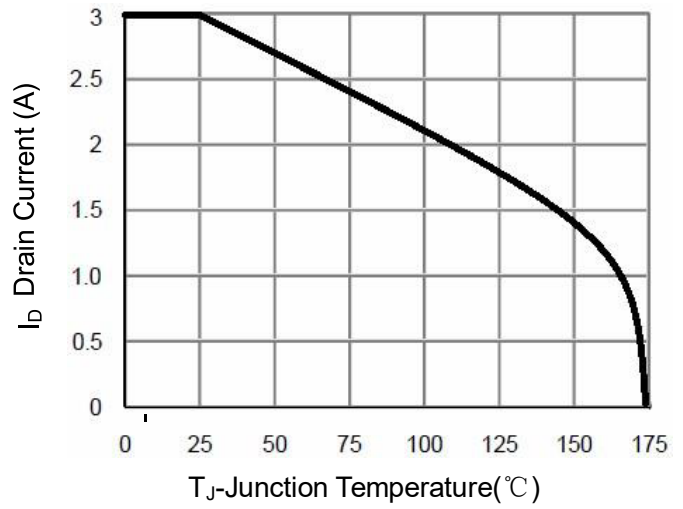


Figure 9 BV_{DSS} vs Junction Temperature

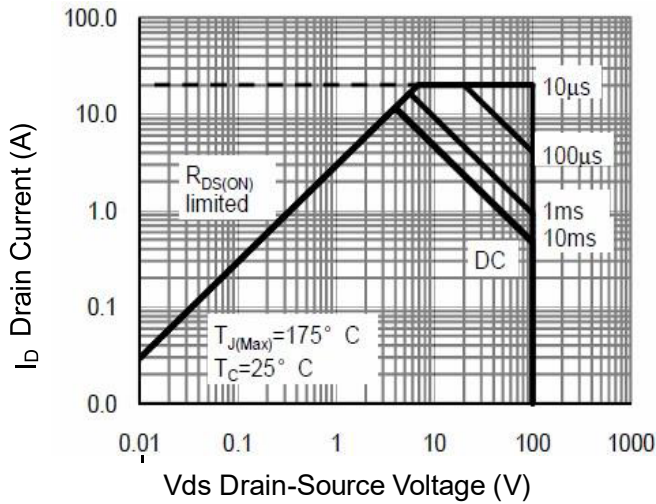


Figure 8 Safe Operation Area

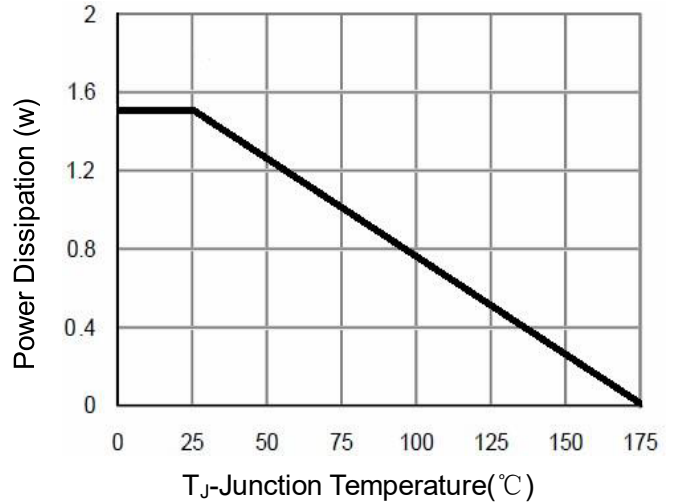


Figure 10 Power De-rating

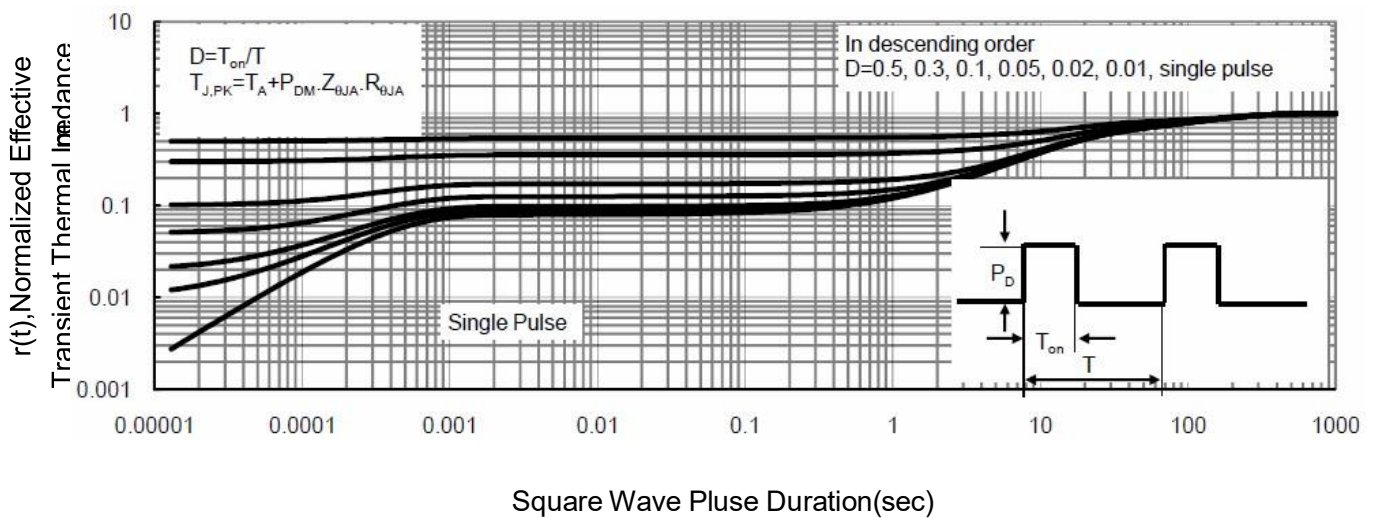
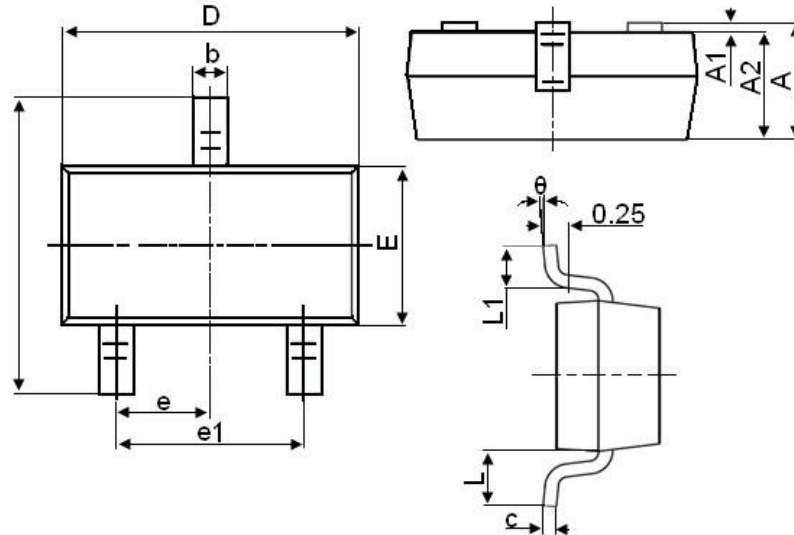


Figure 11 Normalized Maximum Transient Thermal Impedance



SOT23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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